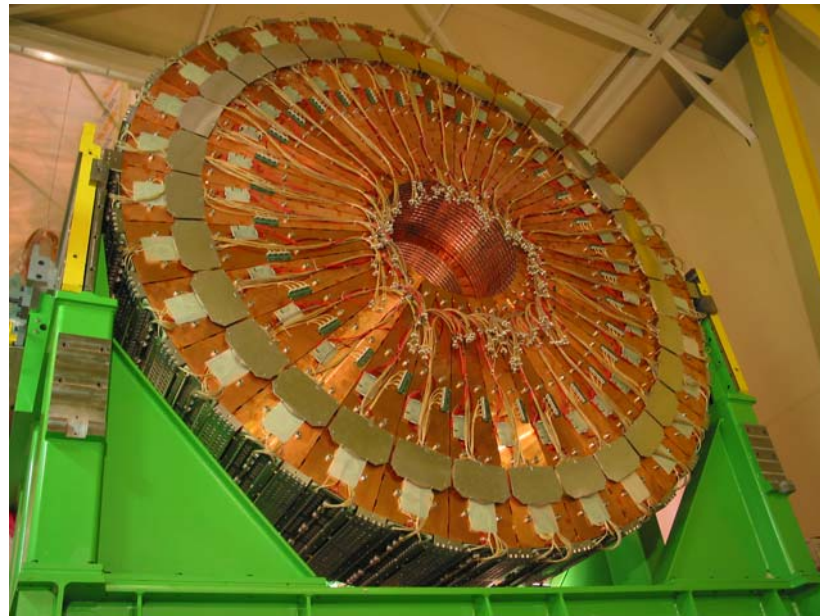


Radiation Hardness of HEC Electronics



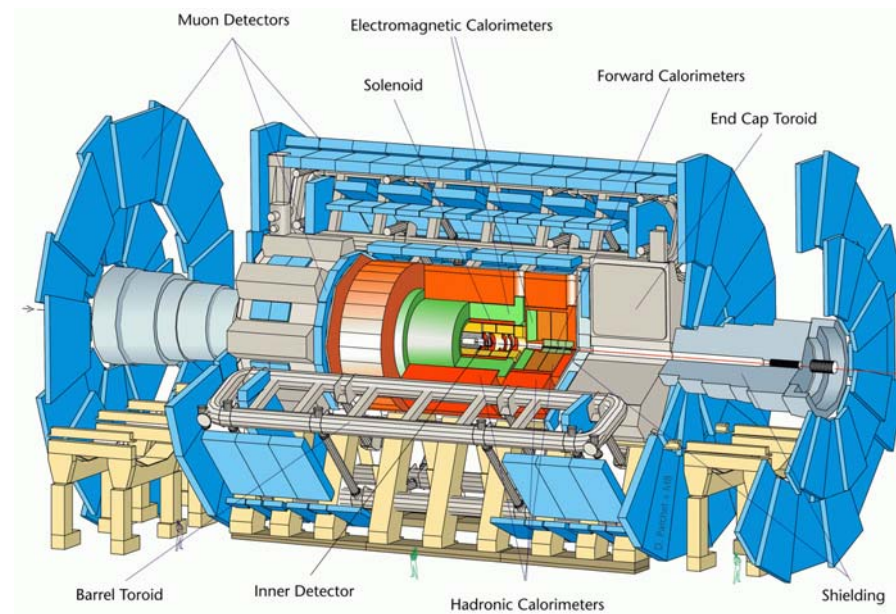
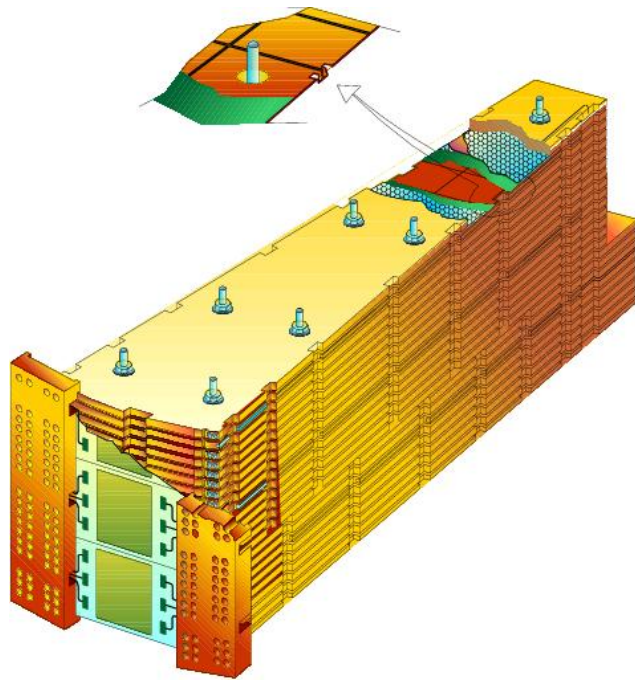
Emanuel Rauter ATLAS HEC

Contents

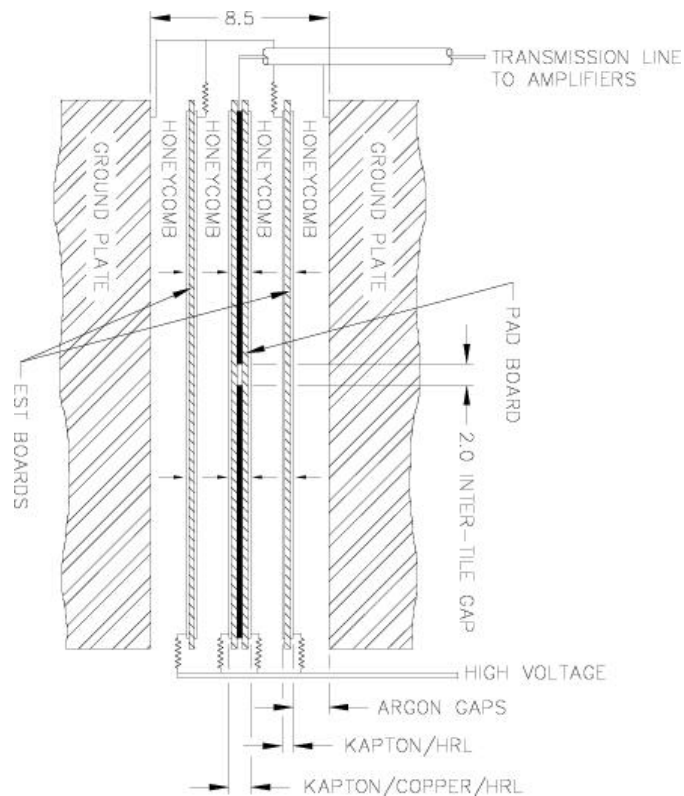
- Calorimeter
- Electronics
- Radiation effects on electronic components
- Test of radiation hardness

The Calorimeter

Hadronic End Cap Calorimeter of ATLAS is a LAr Calorimeter, i.e. Argon as active material, copper plates as absorber material.



Recalling The Principle



- Incoming particles cause shower of secondary particle

=> ionisation of Ar

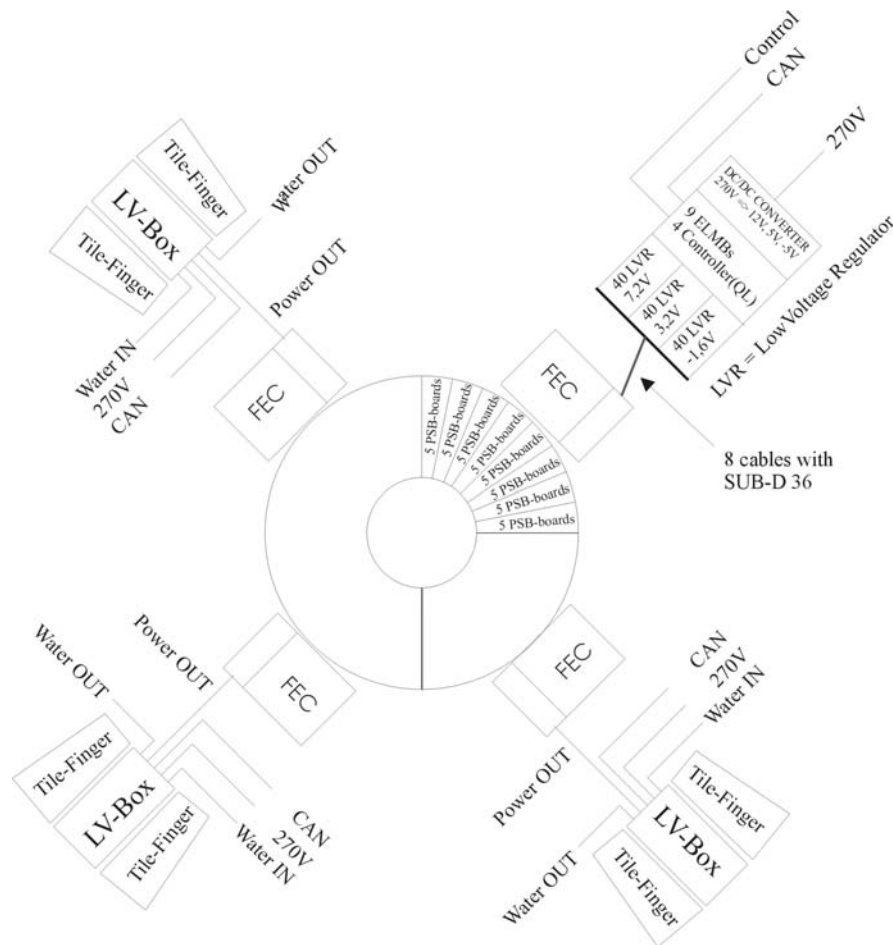
- In electrical field (HV) electrons drift towards electrodes and induce charge.

- Due to the electron drift velocity the signal response is slow (400ns), but rise time of the signal (~1ns) is very short.

Cold Electronics

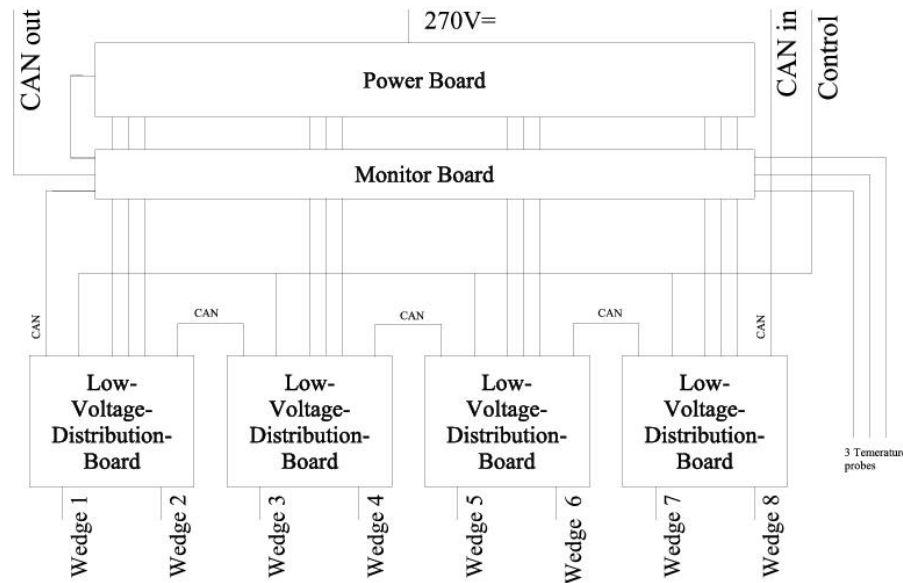
- In conventional LARGCalo the signal rise time is limited by capacitance and inductance of signal cables which are used to sum passive. For ATLAS requirements this would be too slow.
- In HEC summing is done active in direct proximity of the gaps together with the pre amplifying.
- Boards with high integrated GaAs chips positioned on circumference of the HEC wheels.
- Those PSB need to be supplied by a low voltage system.

LV System



- LV System controlled by PVSS
- The boxes are positioned along the outside wall of the cryostat and supplied by 270 V coming from USA15
- Each LV box supplies a quarter of a HEC wheel, meaning 40 PSB.

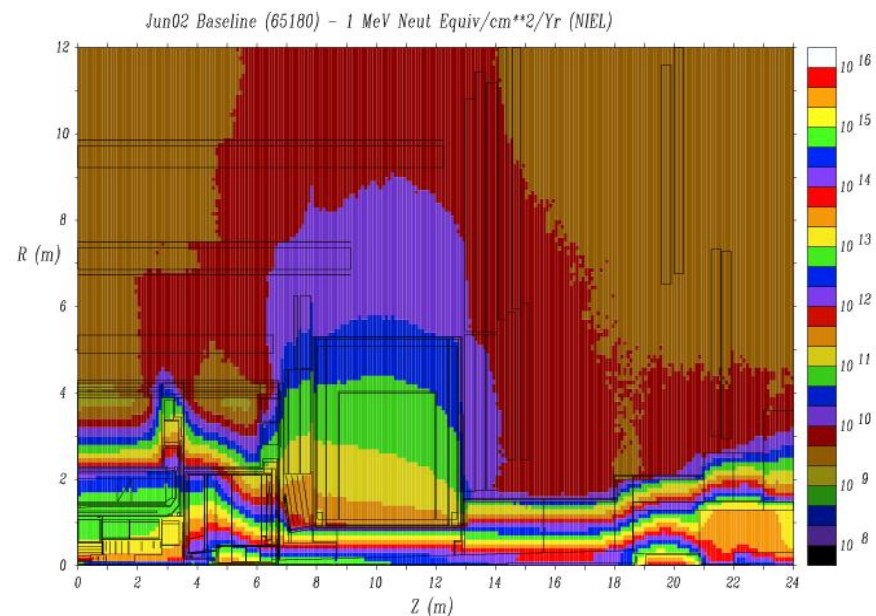
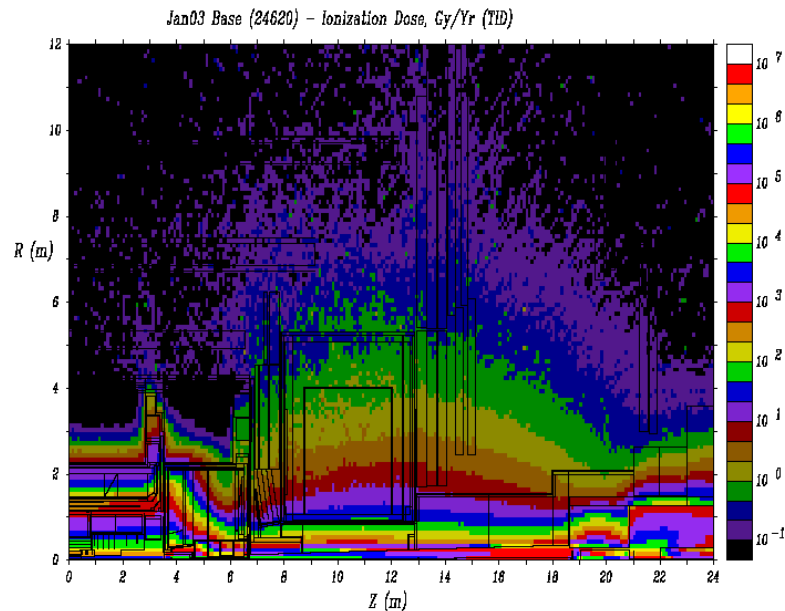
LV Box



- Power board converting the 270 V supply voltage to the middle voltages of 10 / 6 / - 4 V.
- Distribution boards converting the middle voltages to the output voltages of 7,2 / 3,2 / -1,6 V and distributing them to the single PSB.
- One board monitoring the whole box i.e. currents, voltages and temperatures.

Radiation in ATLAS

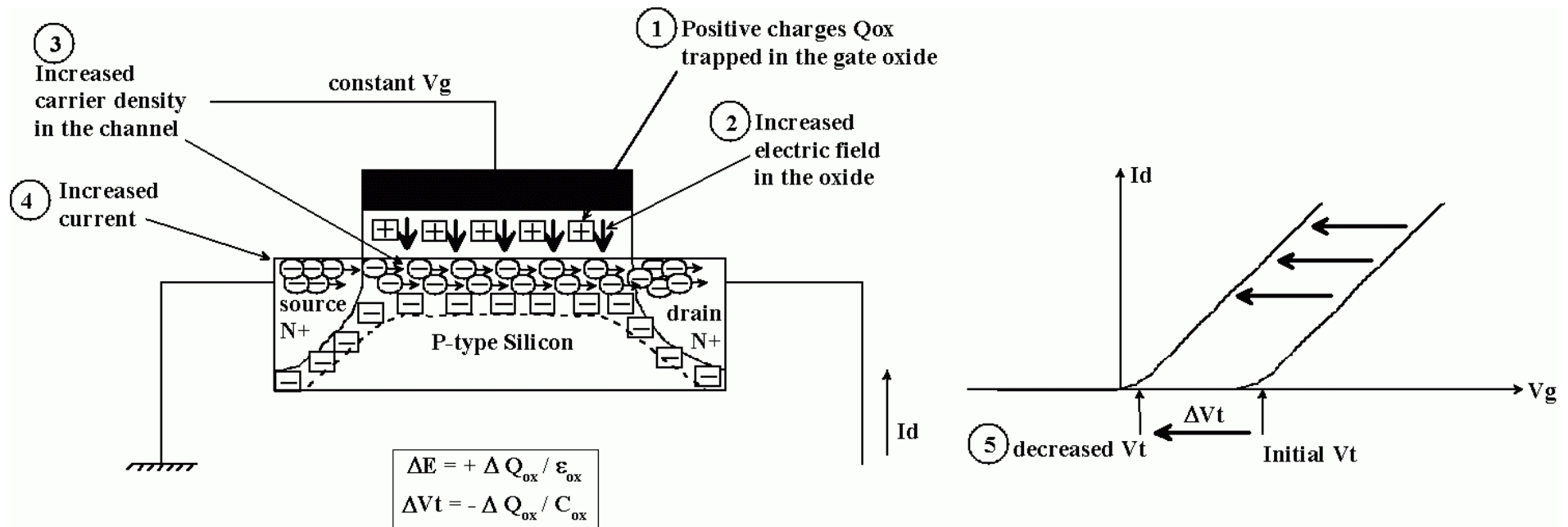
- At high Luminosity running the components will be exposed to a high radiation field of mainly n and γ .
- RHAWG is supplying Simulations and supervising
- For us: 75 Gy and $1,5 \cdot 10^{12} \frac{n}{cm^2}$



Radiation Effects

- Displacement: heavy, neutral particles act on bulk
- Chemical bond rupture photon or charged particle
=> Dangling bonds, recombination centers
- Ionization i.e. electron-hole pair creation: charged particles act on surface
 - instantaneous SEE
=> high e^+e^- density => transient current across oxide
 - accumulated TID
partial recombination, e^+ trapped, e^- leaves oxide
=> long term net positive trapped charges

Threshold Voltage Decrease

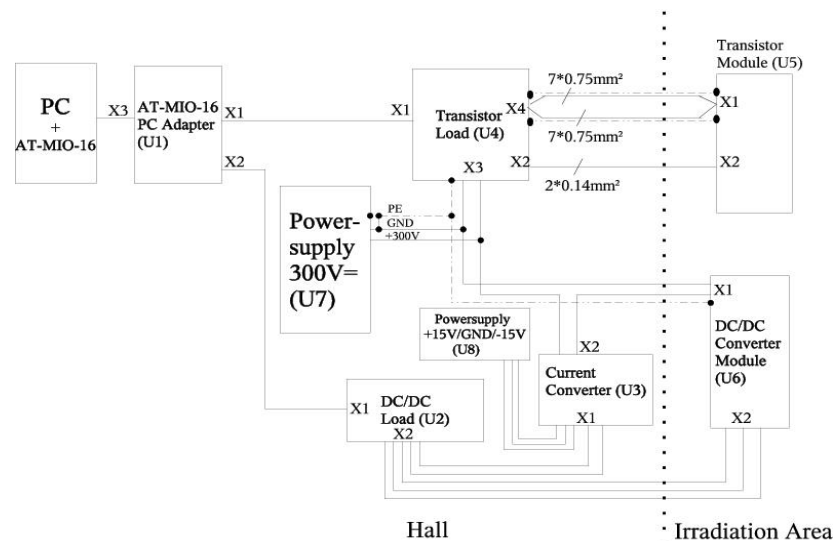


Setup at JINR In Dubna

- Irradiation carried out at pulsed neutron source ИБР-2.
- ИБР-2:
 - Frequency 5 Hz
 - half width of pulse 220 μ s
 - peak power 1500 MW
 - flux 10 Gy/s of γ , $10^{12} \frac{n}{cm^2 s}$
- Since flux is too high in direct beam, the equipment was set up in peripheries.

Measurement

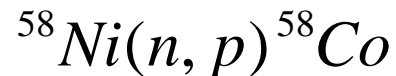
- DC/DC converter module
 - output voltages and input current working under load
- Separate module of power transistors which are used in DC/DC converter
 - switching and measuring drain voltage and current



Dosimetry

- The methods of threshold detector activation were used to determine the neutron fluence.

- Nickel probes placed in irradiation area were activated by the reaction

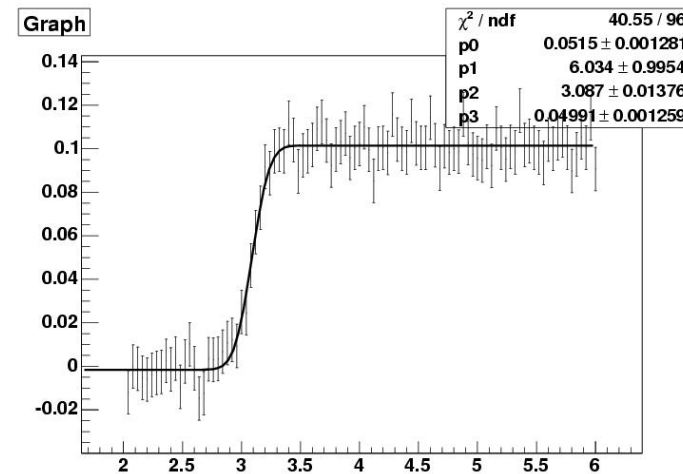
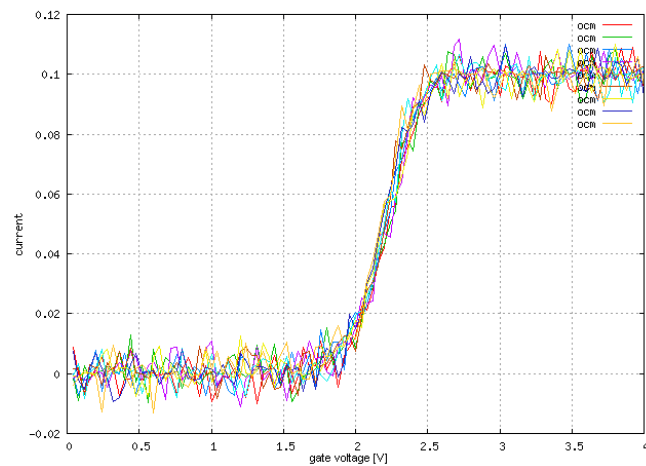


- Induced γ - activity of this reaction was measured with a GeLi detector

Latest values: $6.9 \cdot 10^7 \frac{n}{\text{cm}^2 \text{s}}$ at the position of the DC/DC converter

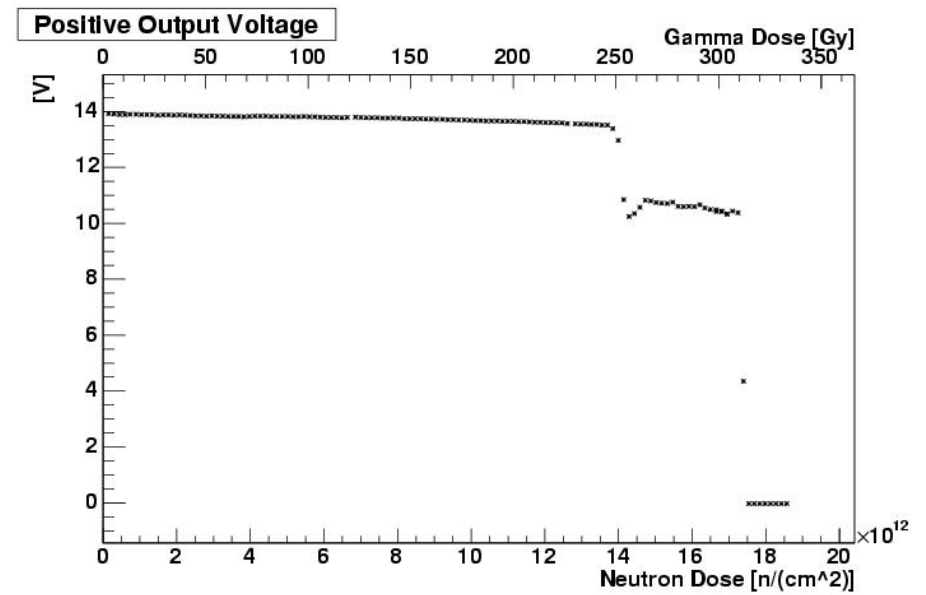
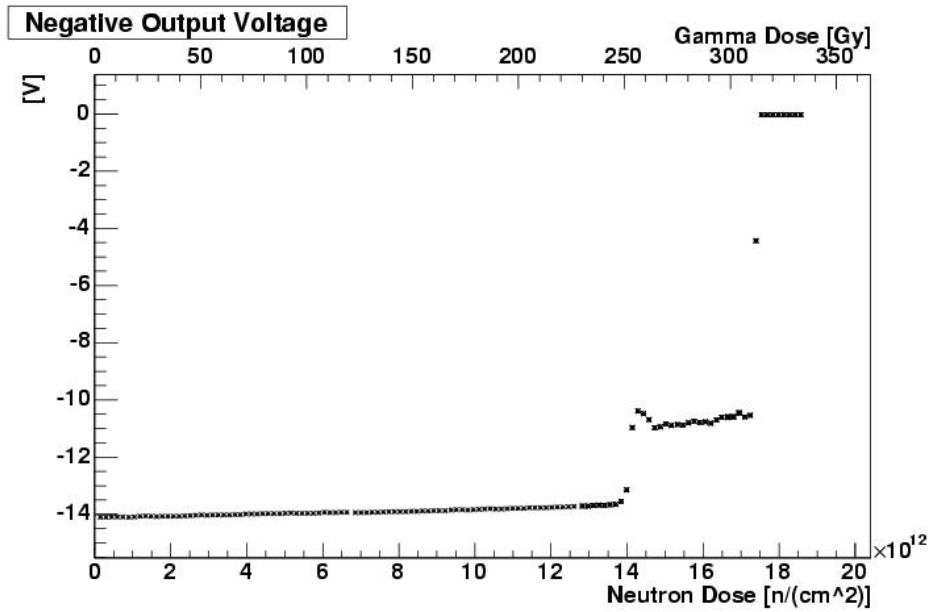
- The γ -dose rate was measured (by some kind of γ -dosimeters) to be 4.9 Gy per hour

Results, Noise

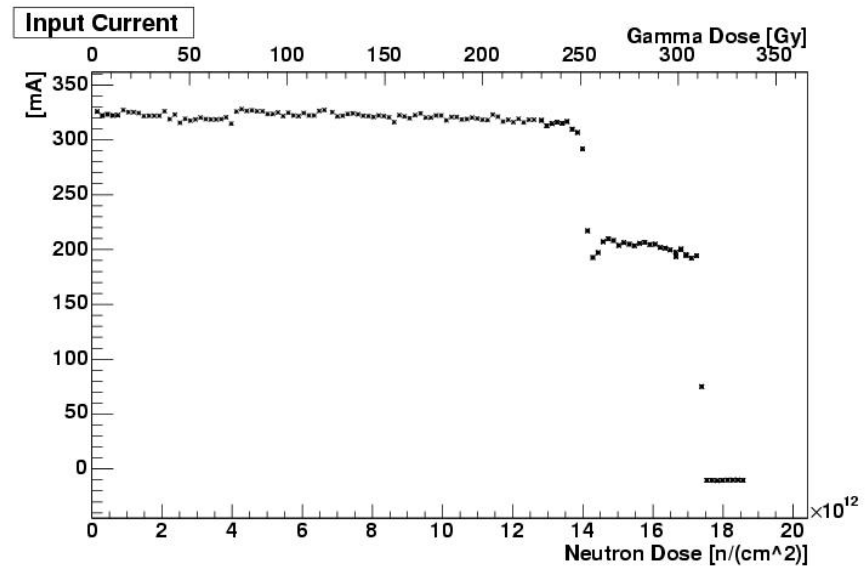
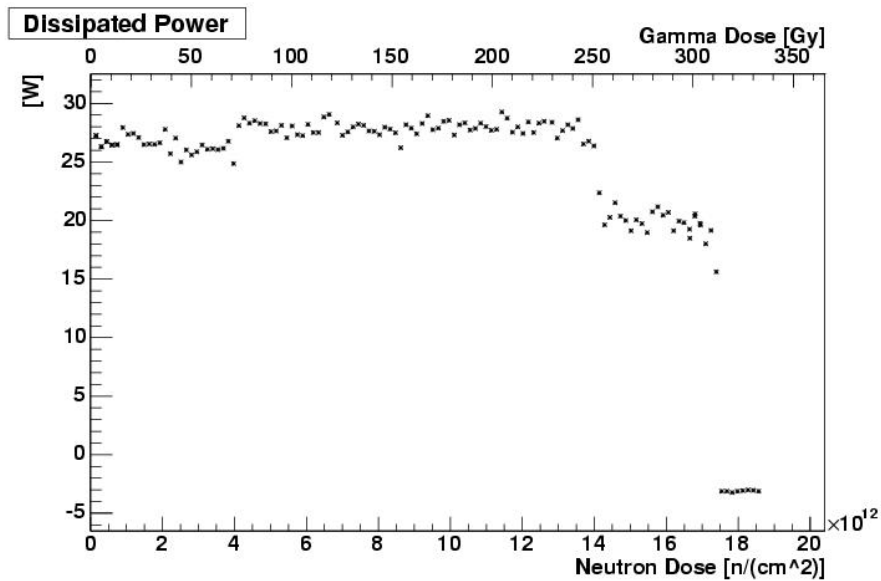


- Unexpected huge, high frequency noise, not well understood, because of 1s sampling
- Data analysis with fit on error function for transistors, averaging for DC/DC converter

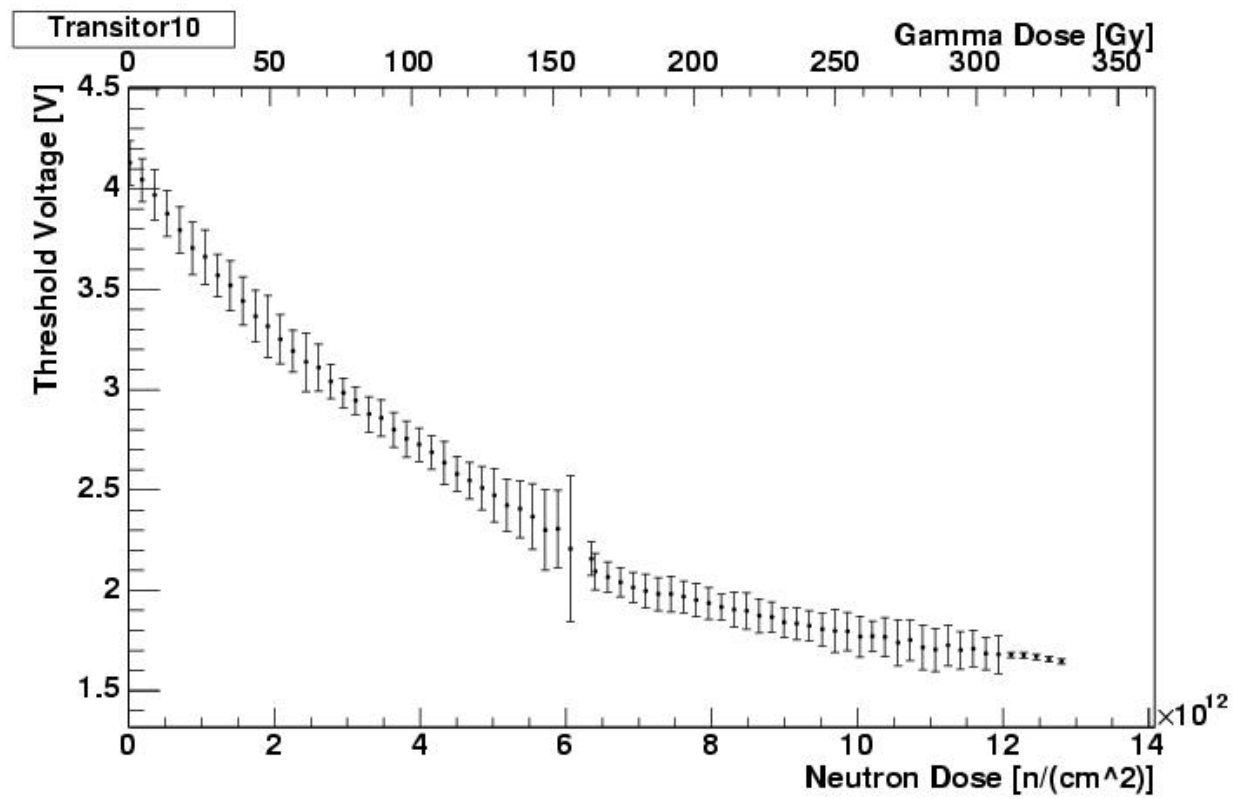
DC/DC Converter



DC/DC Converter



Transistors



Conclusion / Outlook

- Requirements are fulfilled for single modules
- Load transistors not responsible for breakdown of DC/DC converter, probably caused by failure of control transistors
- Next test in Dubna of whole system
- Better understanding of dosimetry is needed
- Other radiation effects SEE to be tested in proton beam

Literature

- Oberlack, Schacht, ATLAS – Ein Schluesselexperiment zum Verstaendnis von Kraefte und Materie, MPI-PhE/2000-27
- Dentan, Radiation Effects on Electronic Components, <http://atlas.web.cern.ch>
- Giustino Radiation Effects on Semiconductor Devices, POLITECNICO DI TORINO I Facoltà di Ingegneria, Marzo 2001
- Cwienk, Habring, Rudert, LV Powersupply, HEC Note 137